

## IGBT Module

Preliminary Data Sheet

### PSIG 75/12

### PSI 75/12\*

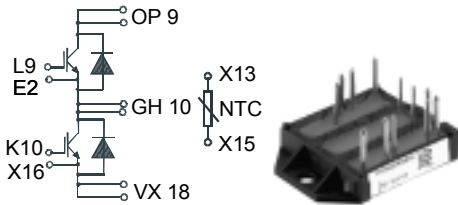
### PSIS 75/12\*

### PSSI 75/12\*

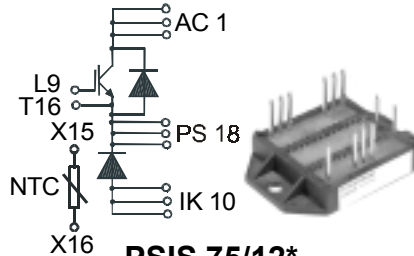
$$I_{C25} = 92 \text{ A}$$

$$V_{CES} = 1200 \text{ V}$$

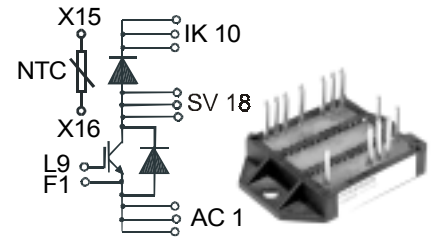
$$V_{CE(sat)typ.} = 2.7 \text{ V}$$



PSI 75/12\*



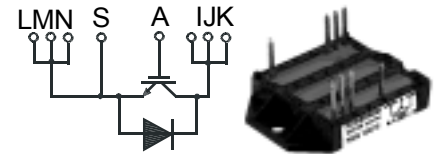
PSIS 75/12\*



PSSI 75/12\*

## IGBTs

Symbol	Conditions	Maximum Ratings
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200 V
$V_{GES}$		$\pm 20$ V
$I_{C25}$	$T_C = 25^{\circ}\text{C}$	92 A
$I_{C80}$	$T_C = 80^{\circ}\text{C}$	62 A
$I_{CM}$ $V_{CEK}$	$V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	100 A $V_{CES}$
$t_{SC}$ (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10 $\mu\text{s}$
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	379 W



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\*NTC optional

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 75 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.7 3.0	V V	
$V_{GE(th)}$	$I_C = 2 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V	
$I_{CES}$	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			3.7 mA 12.5 mA	
$I_{GES}$	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA	
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $E_{on}$ $E_{off}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 60 \text{ A}$ $V_{GE} = 15/0 \text{ V}; R_G = 22 \Omega$		100 70 500 70	ns ns ns ns	
				9.1 6.7	mJ mJ
$C_{ies}$		$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		3.3	nF
$R_{thJC}$ $R_{thJH}$		(per IGBT) with heatsink compound (0.42 K/m.K; 50 $\mu\text{m}$ )		0.66	0.33 K/W K/W

## Features

- Package with DCB ceramic base plate
- Isolation voltage 3000 V~
- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL registered, E 148688

## Applications

- AC and DC motor control
- AC servo and robot drives
- power supplies
- welding inverters

## Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Small and light weight

**Caution:** These Devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

### Reverse diodes (FRED)

Symbol	Conditions	Maximum Ratings	
$I_{F25}$	$T_C = 25^\circ\text{C}$	103	A
$I_{F80}$	$T_C = 80^\circ\text{C}$	65	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 60\text{ A}; T_{VJ} = 25^\circ\text{C}$		2.28	2.6
	$T_{VJ} = 125^\circ\text{C}$		1.67	
$I_{RM}$	$I_F = 60\text{ A}; di_F/dt = 500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$		41	A
$t_{rr}$		$V_R = 600\text{ V}; V_{GE} = 0\text{ V}$		200
$R_{thJC}$	with heatsink compound (0.42 K/m.K; 50 $\mu\text{m}$ )			0.66
$R_{thJH}$				1.32

### Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{25}$	$T = 25^\circ\text{C}$	4.75	5.0	5.25
$B_{25/50}$			3375	K

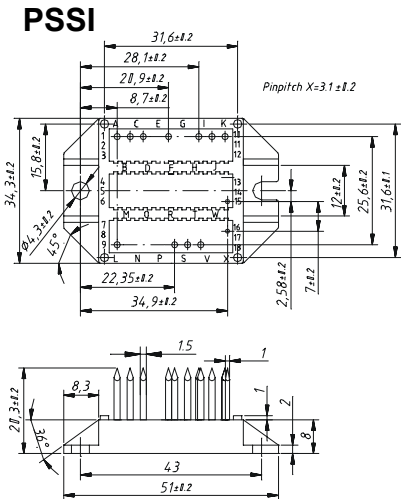
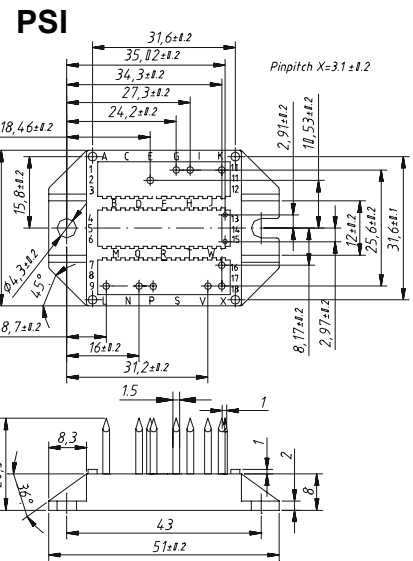
### Module

Symbol	Conditions	Maximum Ratings	
$T_{VJ}$		-40...+150	$^\circ\text{C}$
$T_{stg}$		-40...+150	$^\circ\text{C}$
$V_{ISOL}$	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	3000	V~
$M_d$	Mounting torque (M4)	1.5 - 2.0	Nm
		14 - 18	lb.in.
$a$	Max. allowable acceleration	50	$\text{m/s}^2$

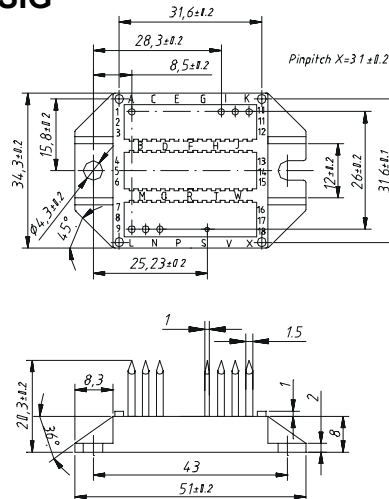
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$d_s$	Creepage distance on surface (Pin to heatsink)	11.2		mm
$d_A$	Strike distance in air (Pin to heatsink)	11.2		mm
Weight			24	g

### Package style and outline

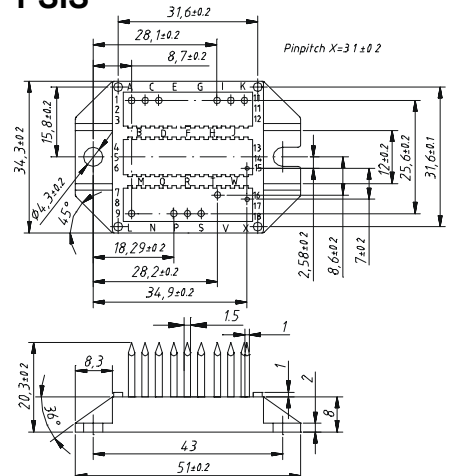
Dimensions in mm (1mm = 0.0394")



### PSIG



### PSIS



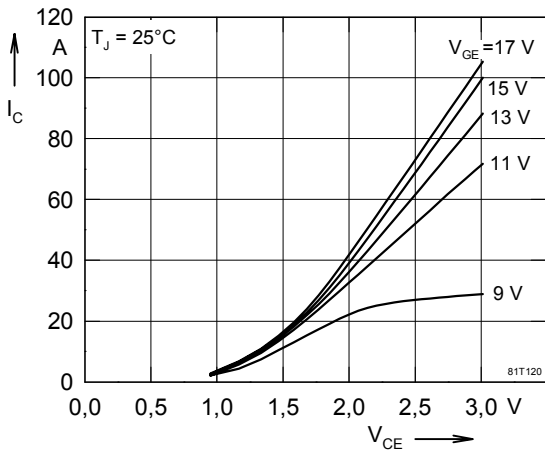


Fig. 1 Typ. output characteristics

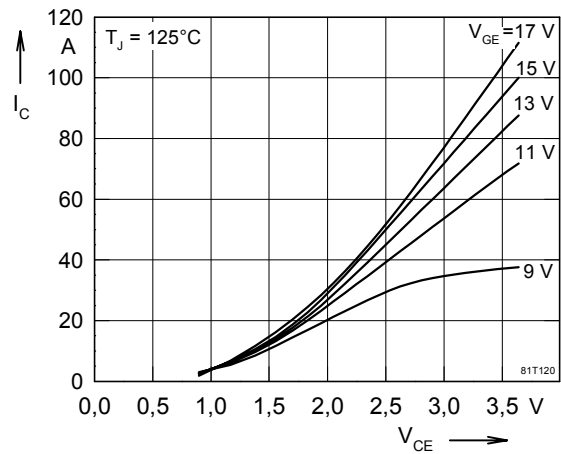


Fig. 2 Typ. output characteristics

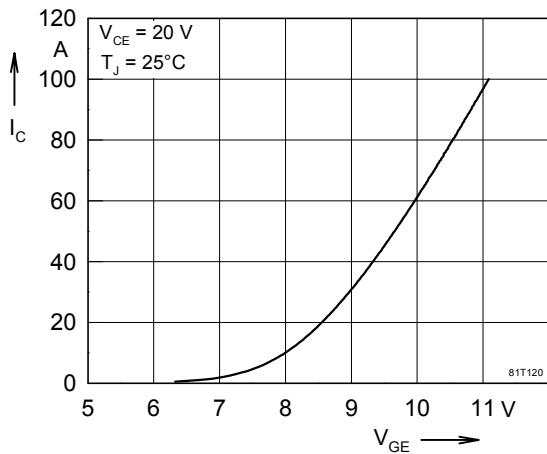


Fig. 3 Typ. transfer characteristics

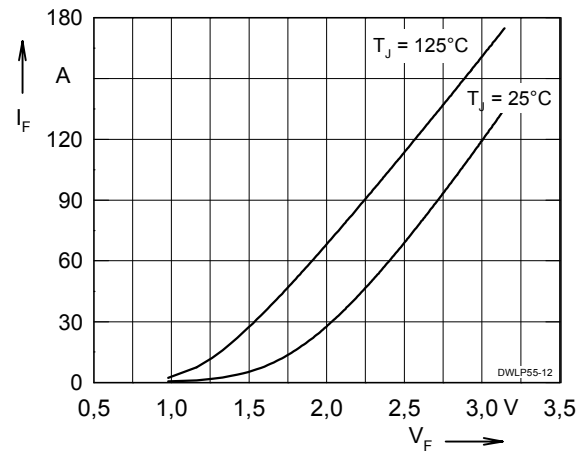


Fig. 4 Typ. forward characteristics of free wheeling diode

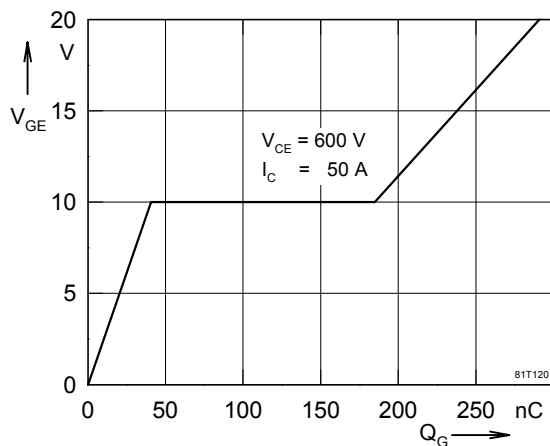


Fig. 5 Typ. turn on gate charge

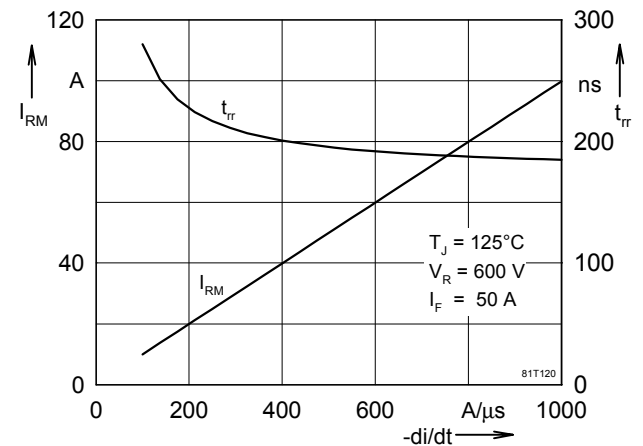


Fig. 6 Typ. turn off characteristics of free wheeling diode

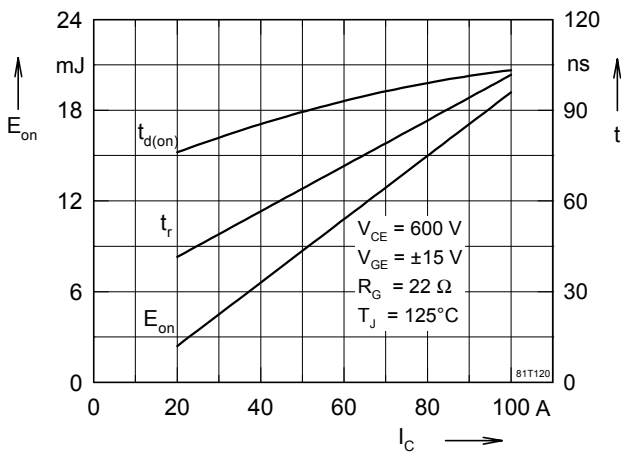


Fig. 7 Typ. turn on energy and switching

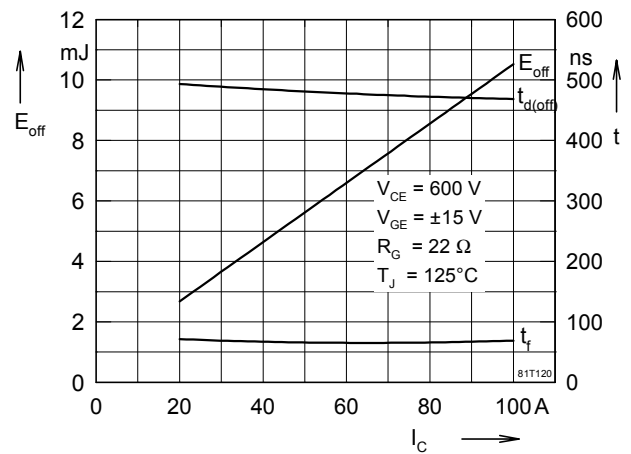


Fig. 8 Typ. turn off energy and switching times versus collector current times versus collector current

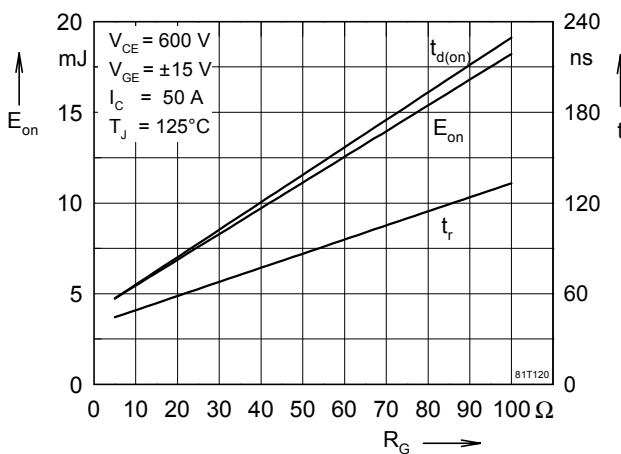


Fig. 9 Typ. turn on energy and switching

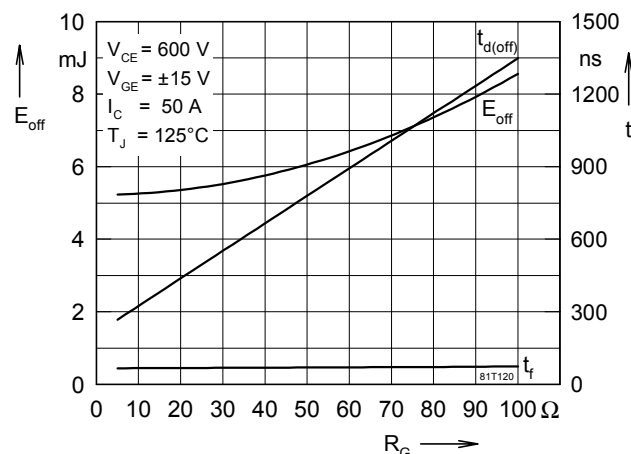


Fig. 10 Typ. turn off energy and switching times versus gate resistor times versus gate resistor

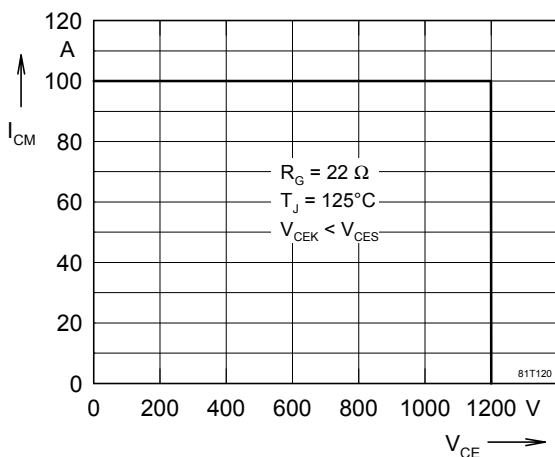


Fig. 11 Reverse biased safe operating area

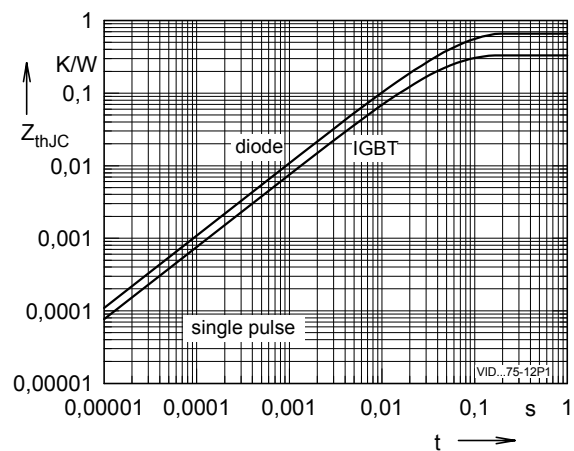


Fig. 12 Typ. transient thermal impedance RBSOA